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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

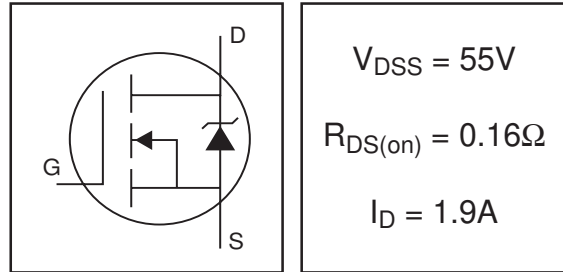
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



IRFL014NPbF

HEXFET® Power MOSFET

- Surface Mount
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



Description

Fifth Generation HEXFET® MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SOT-223 package is designed for surface-mount using vapor phase, infrared, or wave soldering techniques. Its unique package design allows for easy automatic pick-and-place as with other SOT or SOIC packages but has the added advantage of improved thermal performance due to an enlarged tab for heatsinking. Power dissipation of 1.0W is possible in a typical surface mount application.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{**}$	2.7	A
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^*$	1.9	
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^*$	1.5	
I_{DM}	Pulsed Drain Current $\text{\textcircled{1}}$	15	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation (PCB Mount)**	2.1	W
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation (PCB Mount)*	1.0	W
	Linear Derating Factor (PCB Mount)*	8.3	mW/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy $\text{\textcircled{2}}$	48	mJ
I_{AR}	Avalanche Current $\text{\textcircled{3}}$	1.7	A
E_{AR}	Repetitive Avalanche Energy $\text{\textcircled{4}}$	0.1	mJ
dv/dt	Peak Diode Recovery dv/dt $\text{\textcircled{5}}$	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Amb. (PCB Mount, steady state)*	90	120	°C/W
$R_{\theta JA}$	Junction-to-Amb. (PCB Mount, steady state)**	50	60	

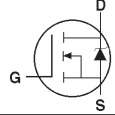
* When mounted on FR-4 board using minimum recommended footprint.

** When mounted on 1 inch square copper board, for comparison with other SMD devices.

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.054	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.16	Ω	V _{GS} = 10V, I _D = 1.9A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	1.6	—	—	S	V _{DS} = 25V, I _D = 0.85A
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 44V, V _{GS} = 0V
		—	—	25		V _{DS} = 44V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	7.0	11	nC	I _D = 1.7A
Q _{gs}	Gate-to-Source Charge	—	1.2	1.8		V _{DS} = 44V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	3.3	5.0		V _{GS} = 10V, See Fig. 6 and 13 ④
t _{d(on)}	Turn-On Delay Time	—	6.6	—	ns	V _{DD} = 28V
t _r	Rise Time	—	7.1	—		I _D = 1.7A
t _{d(off)}	Turn-Off Delay Time	—	12	—		R _G = 6.0Ω
t _f	Fall Time	—	3.3	—		R _D = 16Ω, See Fig. 10 ④
C _{iss}	Input Capacitance	—	190	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	72	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	33	—		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	15		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 1.7A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	41	61	ns	T _J = 25°C, I _F = 1.7A
Q _{rr}	Reverse Recovery Charge	—	64	95	nC	di/dt = 100A/μs ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V_{DD} = 25V, starting T_J = 25°C, L = 8.2mH
R_G = 25Ω, I_{AS} = 3.4A. (See Figure 12)
- ③ I_{SD} ≤ 1.7A, di/dt ≤ 250A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

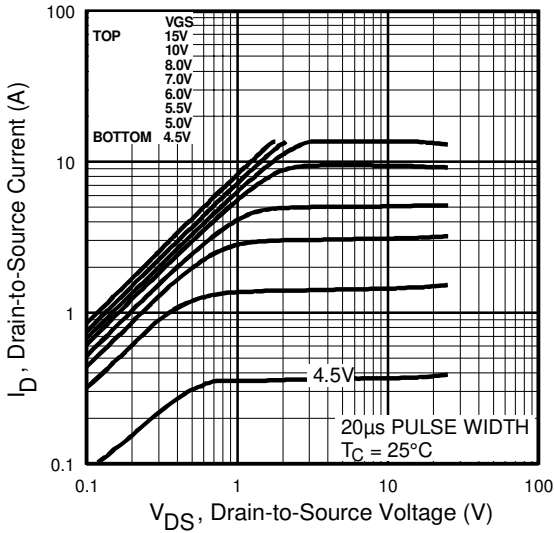


Fig 1. Typical Output Characteristics

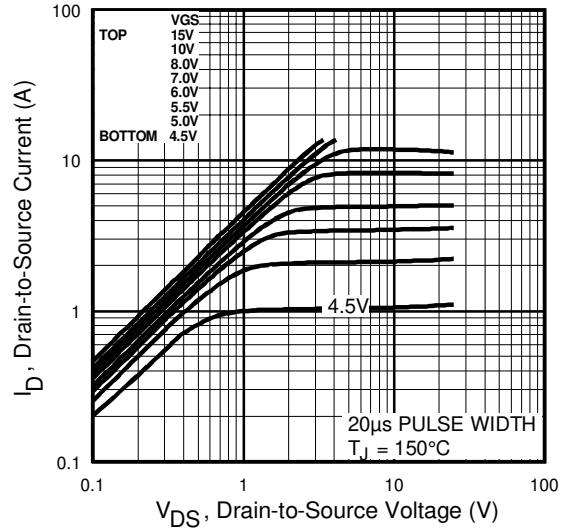


Fig 2. Typical Output Characteristics

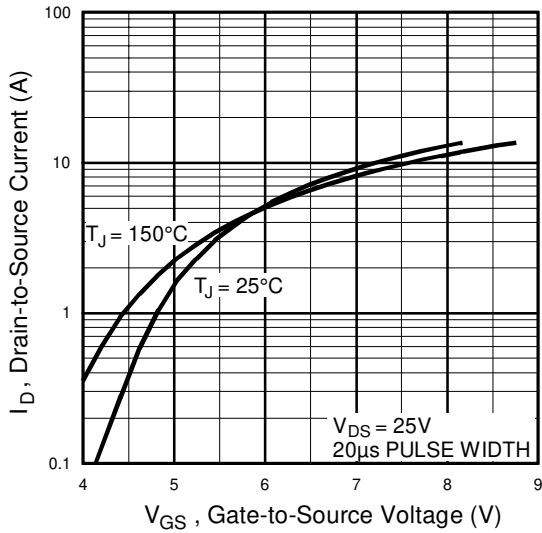


Fig 3. Typical Transfer Characteristics

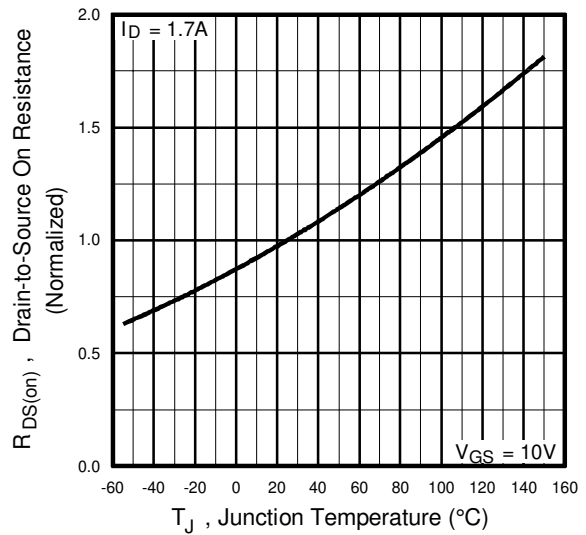


Fig 4. Normalized On-Resistance Vs. Temperature

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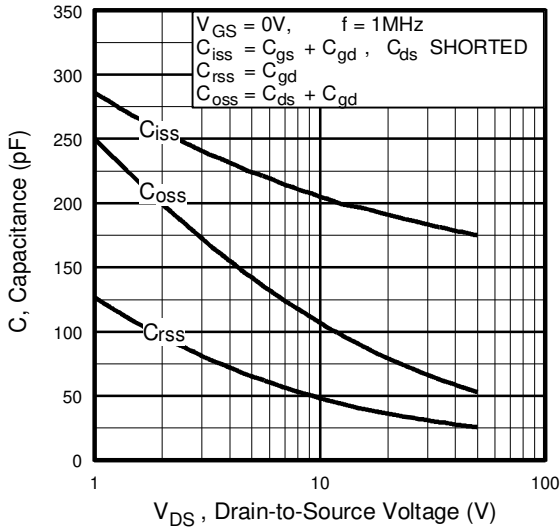


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

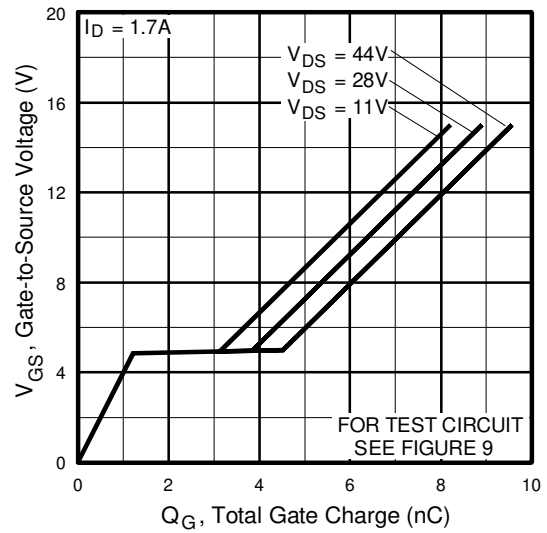


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

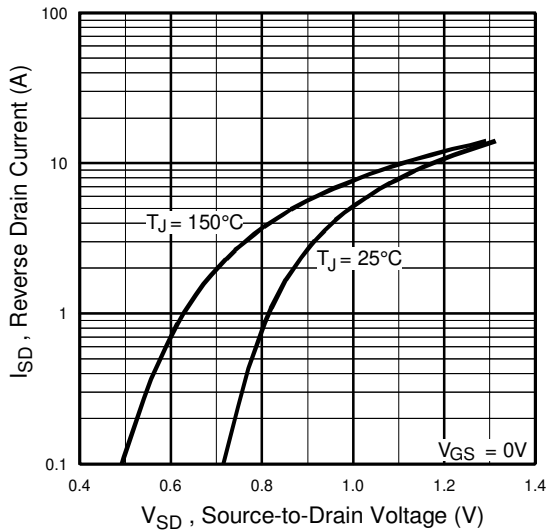


Fig 7. Typical Source-Drain Diode Forward Voltage

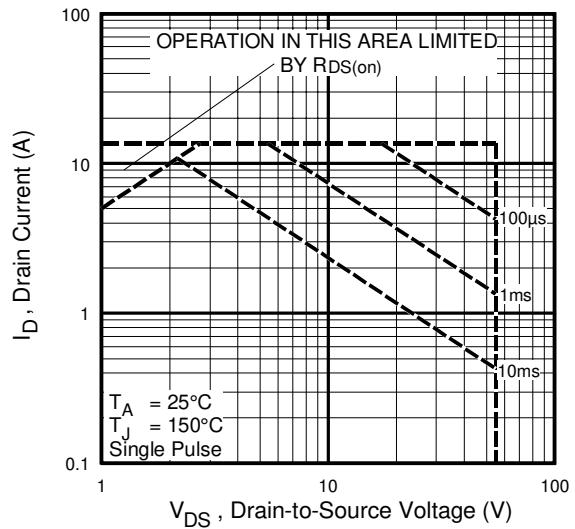


Fig 8. Maximum Safe Operating Area

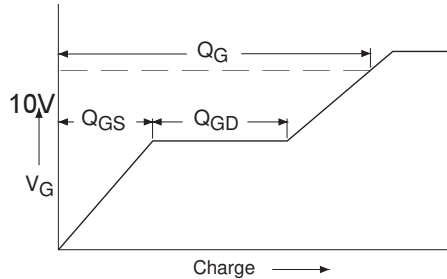


Fig 9a. Basic Gate Charge Waveform

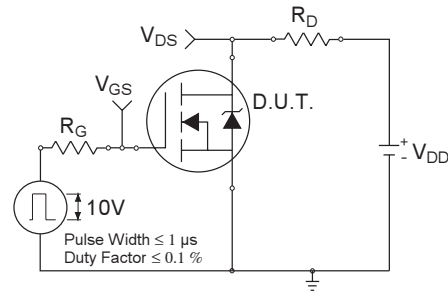


Fig 10a. Switching Time Test Circuit

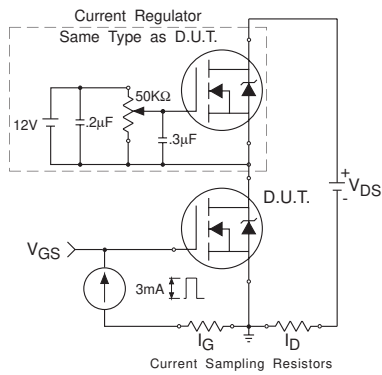


Fig 9b. Gate Charge Test Circuit

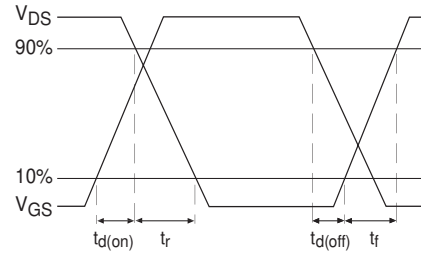


Fig 10b. Switching Time Waveforms

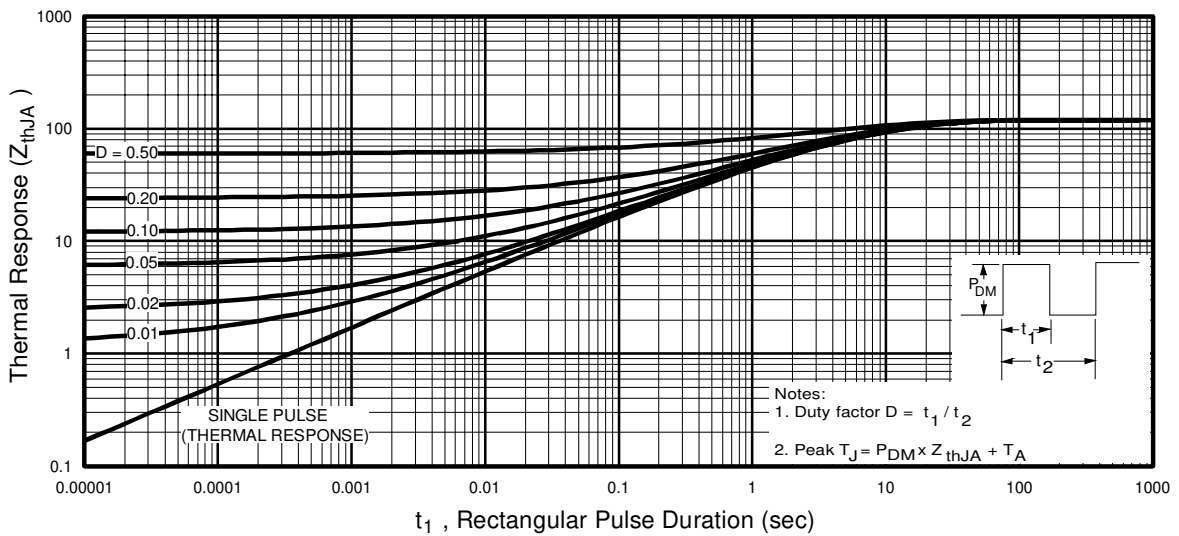


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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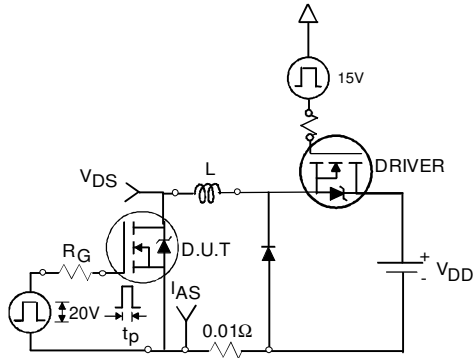


Fig 12a. Unclamped Inductive Test Circuit

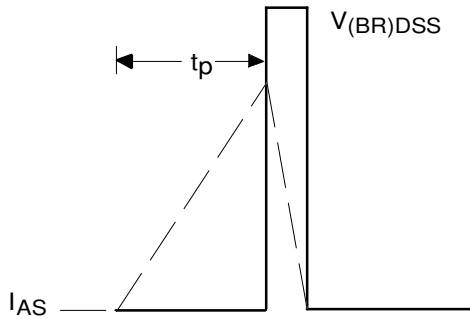


Fig 12b. Unclamped Inductive Waveforms

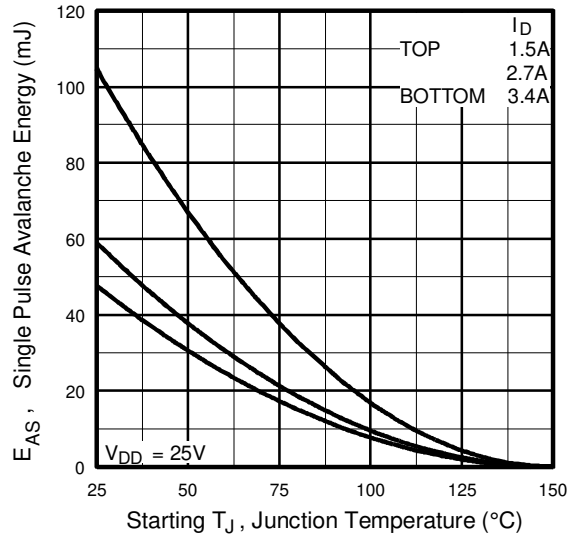
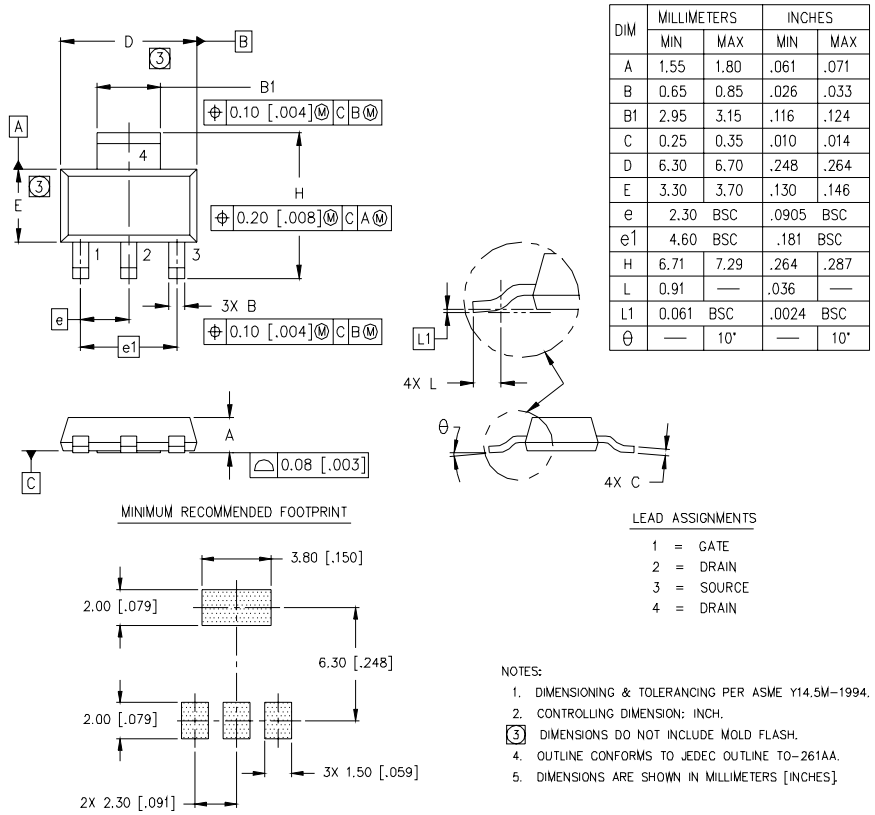


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

SOT-223 (TO-261AA) Package Outline

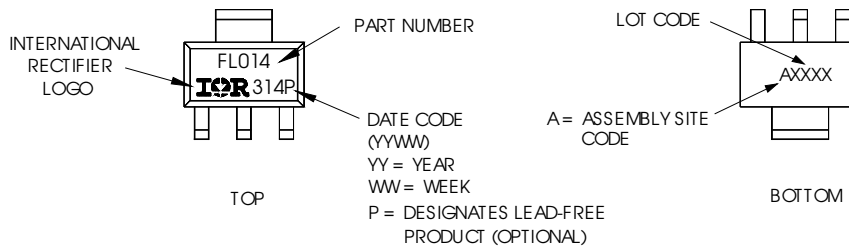
Dimensions are shown in millimeters (inches)



SOT-223 (TO-261AA) Part Marking Information

HEXFET PRODUCT MARKING

EXAMPLE: THIS IS AN IRFL014

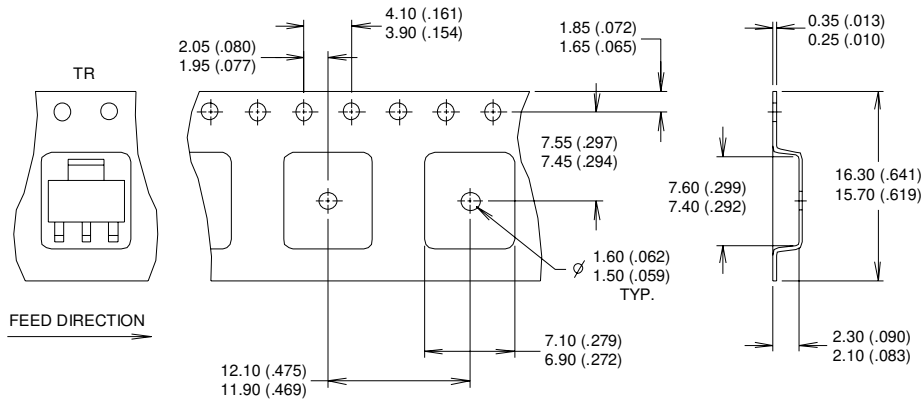


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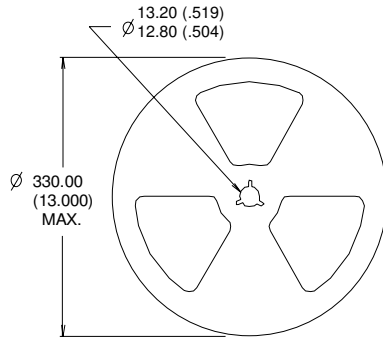
SOT-223 (TO-261AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



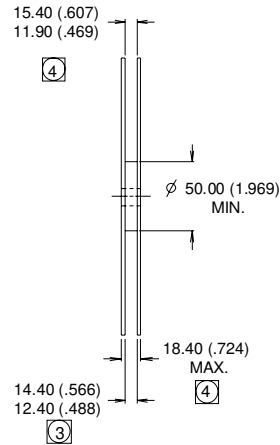
NOTES :

1. CONTROLLING DIMENSION: MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.
3. EACH $\varnothing 330.00$ (13.00) REEL CONTAINS 2,500 DEVICES.



NOTES :

1. OUTLINE CONFORMS TO EIA-418-1.
2. CONTROLLING DIMENSION: MILLIMETER..
- ③ DIMENSION MEASURED @ HUB.
- ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.



Data and specifications subject to change without notice.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

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